



Key Parameters

V_{DRM} / V_{RRM}	1800 V
I_{TAVM}	190 A ($T_C=85\text{ }^\circ\text{C}$)
I_{TSM}	5200 A
V_{T0}	0,85 V
r_T	0,9 m Ω
R_{thJC}	0,145 K/W
Base plate	34 mm
Weight	165 g



For type designation please refer to actual short form catalog

<http://www.ifbip.com/catalog>

Merkmale

- Löt-Bond Technologie
- Industrie-Standard-Gehäuse
- Elektrisch isolierte Bodenplatte

Features

- Solder-Bond Technology
- Industrial standard package
- Electrically insulated base plate

Typische Anwendungen

- Sanftanlasser
- Gleichrichter für Antriebsapplikationen
- Leistungssteller
- Gleichrichter für UPS
- Batterieladegleichrichter
- Statische Umschalter

Typical Applications

- Soft starter
- Rectifier for drives applications
- Power controllers
- Rectifiers for UPS
- Battery chargers
- Static switches

content of customer DMX code	DMX code digit	DMX code digit quantity
type designation	1..18	18
serial number	19..23	5
internal production order number	24..31	8
material number	32..41	10
date code (YY/WW)	42..45	4
add on for date code	46	1



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Technische Information / technical information



Netz-Thyristor-Modul
Phase Control Thyristor Module

TT190N18SOF

Infineon Technologies Bipolar
GmbH & Co. KG

TT190N18SOF

TD190N18SOF

Elektrische Eigenschaften / Electrical properties

Höchstzulässige Werte / Maximum rated values

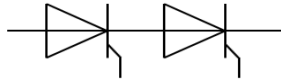
Periodische Vorwärts- und Rückwärts-Spitzensperrspannung repetitive peak forward off-state and reverse voltages	$T_{vj} = +25^{\circ}\text{C} \dots T_{vj\text{max}}^{*1)}$	$V_{\text{DRM}}, V_{\text{RRM}}$	1800	V
Vorwärts-Stoßspitzensperrspannung non-repetitive peak forward off-state voltage	$T_{vj} = +25^{\circ}\text{C} \dots T_{vj\text{max}}$	V_{DSM}	1800	V
Rückwärts-Stoßspitzensperrspannung non-repetitive peak reverse voltage	$T_{vj} = +25^{\circ}\text{C} \dots T_{vj\text{max}}$	V_{RSM}	1900	V
Durchlaßstrom-Grenzeffektivwert maximum RMS on-state current		I_{TRMSM}	275	A
Dauergrenzstrom average on-state current	$T_{\text{C}} = 85^{\circ}\text{C}$	I_{TAVM}	190	A
Stoßstrom-Grenzwert surge current	$T_{vj} = 25^{\circ}\text{C}, t_{\text{P}} = 10\text{ms}$ $T_{vj} = T_{vj\text{max}}, t_{\text{P}} = 10\text{ms}$	I_{TSM}	5200 4500	A A
Grenzlastintegral I^2t -value	$T_{vj} = 25^{\circ}\text{C}, t_{\text{P}} = 10\text{ms}$ $T_{vj} = T_{vj\text{max}}, t_{\text{P}} = 10\text{ms}$	I^2t	135200 101250	A^2s A^2s
Kritische Stromsteilheit critical rate of rise of on-state current	DIN IEC 747-6 $f = 50\text{Hz}, i_{\text{GM}} = 1\text{A}, di_{\text{G}}/dt = 1\text{A}/\mu\text{s}$	$(di_{\text{T}}/dt)_{\text{cr}}$	100	$\text{A}/\mu\text{s}$
Kritische Spannungssteilheit critical rate of rise of off-state voltage	$T_{vj} = T_{vj\text{max}}, V_{\text{D}} = 0,67 V_{\text{DRM}}$ 6.Kennbuchstabe / 6 th letter F	$(dv_{\text{D}}/dt)_{\text{cr}}$	1000	$\text{V}/\mu\text{s}$

Charakteristische Werte / Characteristic values

Durchlaßspannung on-state voltage	$T_{vj} = T_{vj\text{max}}, I_{\text{T}} = 500\text{A}$	V_{T}	max. 1,52	V
Schleusenspannung threshold voltage	$T_{vj} = T_{vj\text{max}}$	$V_{(\text{TO})}$	max. 0,85	V
Ersatzwiderstand slope resistance	$T_{vj} = T_{vj\text{max}}$	r_{T}	max. 0,9	$\text{m}\Omega$
Zündstrom gate trigger current	$T_{vj} = 25^{\circ}\text{C}, V_{\text{D}} = 12\text{V}$	I_{GT}	max. 145	mA
Zündspannung gate trigger voltage	$T_{vj} = 25^{\circ}\text{C}, V_{\text{D}} = 12\text{V}$	V_{GT}	max. 2,5	V
Nicht zündender Steuerstrom gate non-trigger current	$T_{vj} = T_{vj\text{max}}, V_{\text{D}} = 12\text{V}$ $T_{vj} = T_{vj\text{max}}, V_{\text{D}} = 0,5 V_{\text{DRM}}$	I_{GD}	max. 10 max. 5	mA mA
Nicht zündende Steuerspannung gate non-trigger voltage	$T_{vj} = T_{vj\text{max}}, V_{\text{D}} = 0,5 V_{\text{DRM}}$	V_{GD}	max. 0,25	V
Haltestrom holding current	$T_{vj} = 25^{\circ}\text{C}, V_{\text{D}} = 12\text{V}, R_{\text{A}} = 1\Omega$	I_{H}	max. 200	mA
Einraststrom latching current	$T_{vj} = 25^{\circ}\text{C}, V_{\text{D}} = 12\text{V}, R_{\text{GK}} \geq 10\Omega$ $i_{\text{GM}} = 1\text{A}, di_{\text{G}}/dt = 1\text{A}/\mu\text{s}, t_{\text{g}} = 20\mu\text{s}$	I_{L}	max. 400	mA
Vorwärts- und Rückwärts-Sperrstrom forward off-state and reverse current	$T_{vj} = T_{vj\text{max}}$ $V_{\text{D}} = V_{\text{DRM}}, V_{\text{R}} = V_{\text{RRM}}$	$i_{\text{D}}, i_{\text{R}}$	max. 30	mA
Zündverzug gate controlled delay time	DIN IEC 747-6 $T_{vj} = 25^{\circ}\text{C}, i_{\text{GM}} = 1\text{A}, di_{\text{G}}/dt = 1\text{A}/\mu\text{s}$	t_{gd}	max. 2	μs

*1.) Derating factor of 0,154% per K for T_{vj} below 25°C

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Elektrische Eigenschaften / Electrical properties


Charakteristische Werte / Characteristic values

Freiwerdezeit circuit commutated turn-off time	$T_{vj} = T_{vj\max}$, $i_{TM} = I_{TAVM}$ $V_{RM} = 100\text{ V}$, $v_{DM} = 0,67 V_{DRM}$ $dv_D/dt = 20\text{ V}/\mu\text{s}$, $-di_T/dt = 10\text{ A}/\mu\text{s}$ 5.Kennbuchstabe / 5 th letter O	t_q	typ.	320	μs
Isolations-Prüfspannung insulation test voltage	RMS, $f = 50\text{ Hz}$, $t = 1\text{ min}$ RMS, $f = 50\text{ Hz}$, $t = 1\text{ sec}$	V_{ISOL}		3,0 3,6	kV kV

Thermische Eigenschaften / Thermal properties

Innerer Wärmewiderstand thermal resistance, junction to case	pro Modul / per Module, $\Theta = 180^\circ\text{ sin}$ pro Zweig / per arm, $\Theta = 180^\circ\text{ sin}$ pro Modul / per Module, DC pro Zweig / per arm, DC	R_{thJC}	max.	0,0825	K/W
			max.	0,165	K/W
			max.	0,0725	K/W
			max.	0,145	K/W
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro Modul / per Module pro Zweig / per arm	R_{thCH}	max.	0,04	K/W
			max.	0,08	K/W
Höchstzulässige Sperrschichttemperatur maximum junction temperature		$T_{vj\max}$		125	$^\circ\text{C}$
Betriebstemperatur operating temperature		$T_{c\text{ op}}$		-40...+125	$^\circ\text{C}$
Lagertemperatur storage temperature		T_{stg}		-40...+125	$^\circ\text{C}$

Mechanische Eigenschaften / Mechanical properties

Gehäuse, siehe Anlage case, see annex				Seite 4 page 4	
Innere Isolation internal insulation	Basisisolierung (Schutzklasse 1, EN61140) Basic insulation (class 1, IEC61140)			Al_2O_3	
Anzugsdrehmoment für mechanische Anschlüsse mounting torque	Toleranz / Tolerance $\pm 15\%$	M1		5	Nm
Anzugsdrehmoment für elektrische Anschlüsse terminal connection torque	Toleranz / Tolerance $\pm 10\%$	M2		5	Nm
Steueranschlüsse control terminals	DIN 46 244			A 2,8 x 0,8	
Gewicht weight		G	typ.	165	g
Kriechstrecke creepage distance				10	mm
Schwingfestigkeit vibration resistance	$f = 50\text{ Hz}$			50	m/s^2
	file-No.			E 83335	



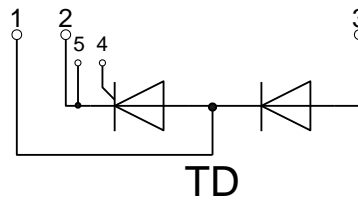
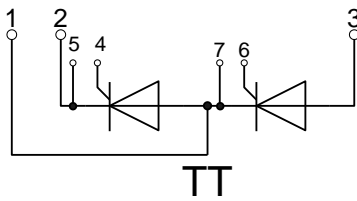
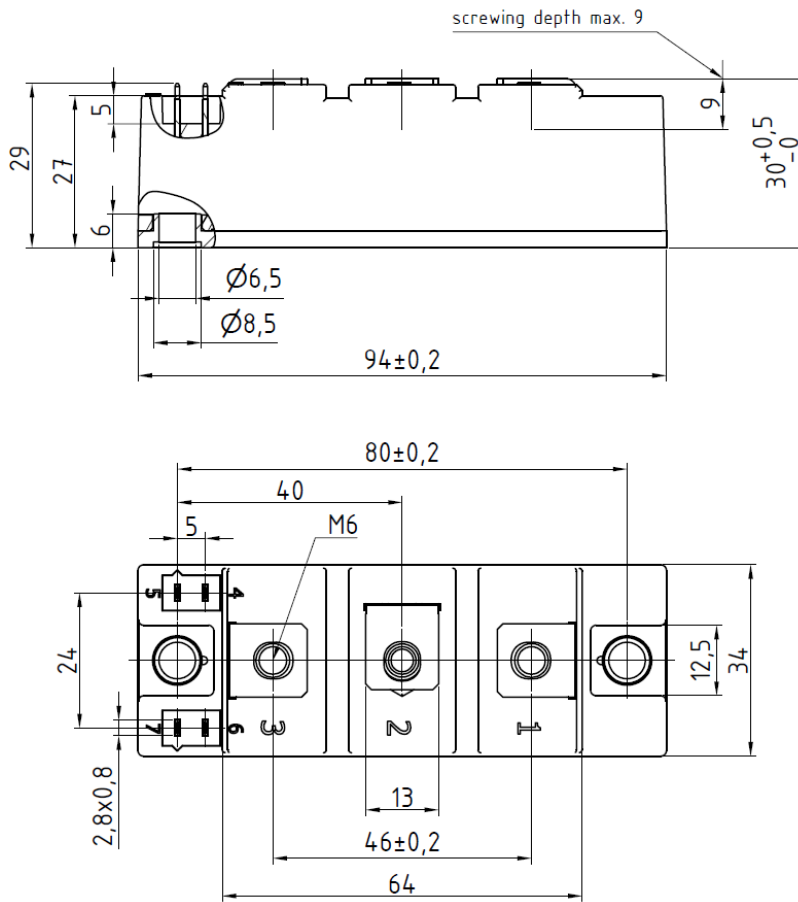
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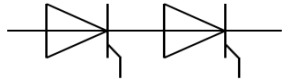


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Analytische Elemente des transienten Wärmewiderstandes Z_{thJC} für DC
Analytical elements of transient thermal impedance Z_{thJC} for DC

Pos. n	1	2	3	4	5	6	7
R_{thn} [K/W]	0,0669	0,0024648	0,0674976	0,0076896			
τ_n [s]	0,035107	0,035092	0,034917	0,001473			

Analytische Funktion / Analytical function:

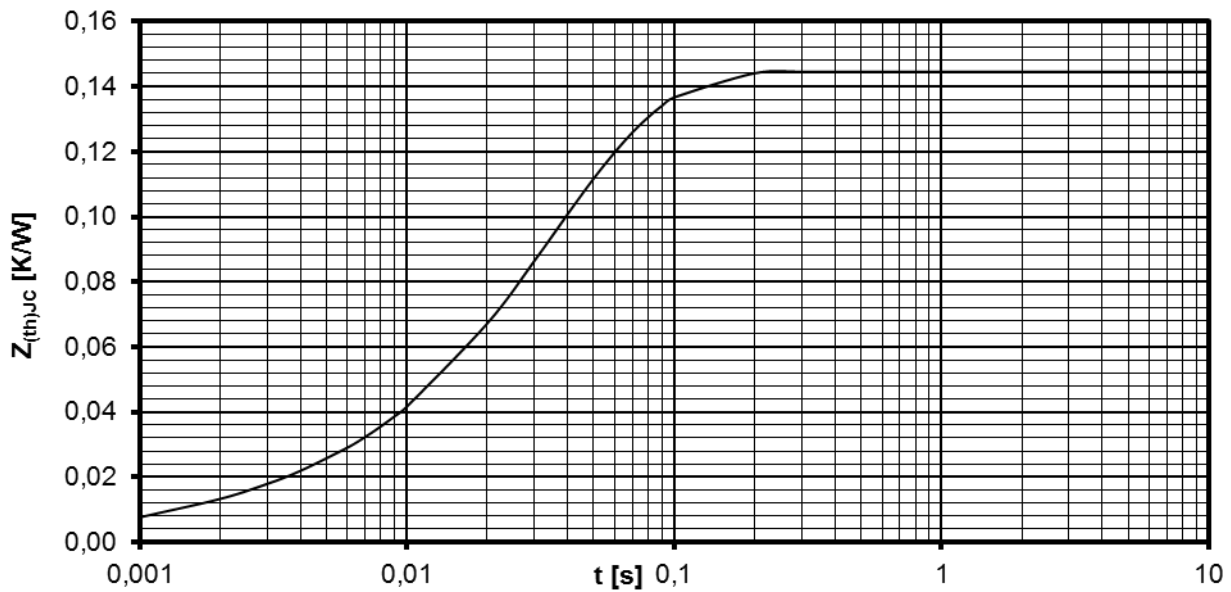
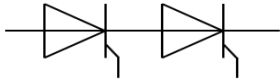
$$Z_{thJC} = \sum_{n=1}^{n_{max}} R_{thn} \left(1 - e^{-\frac{t}{\tau_n}} \right)$$

Erhöhung des Z_{thDC} bei Sinus und Rechteckströmen mit unterschiedlichen Stromflusswinkeln Θ
Rise of Z_{thDC} for sinewave and rectangular current with different current conduction angles Θ
 $\Delta Z_{th \Theta rec} / \Delta Z_{th \Theta sin}$

	$\Theta = 180^\circ$	$\Theta = 120^\circ$	$\Theta = 90^\circ$	$\Theta = 60^\circ$	$\Theta = 30^\circ$
$\Delta Z_{th \Theta rec}$ [K/W]	0,02709	0,04187	0,05259	0,06819	0,09344
$\Delta Z_{th \Theta sin}$ [K/W]	0,02071	0,02767	0,03665	0,05160	0,08004

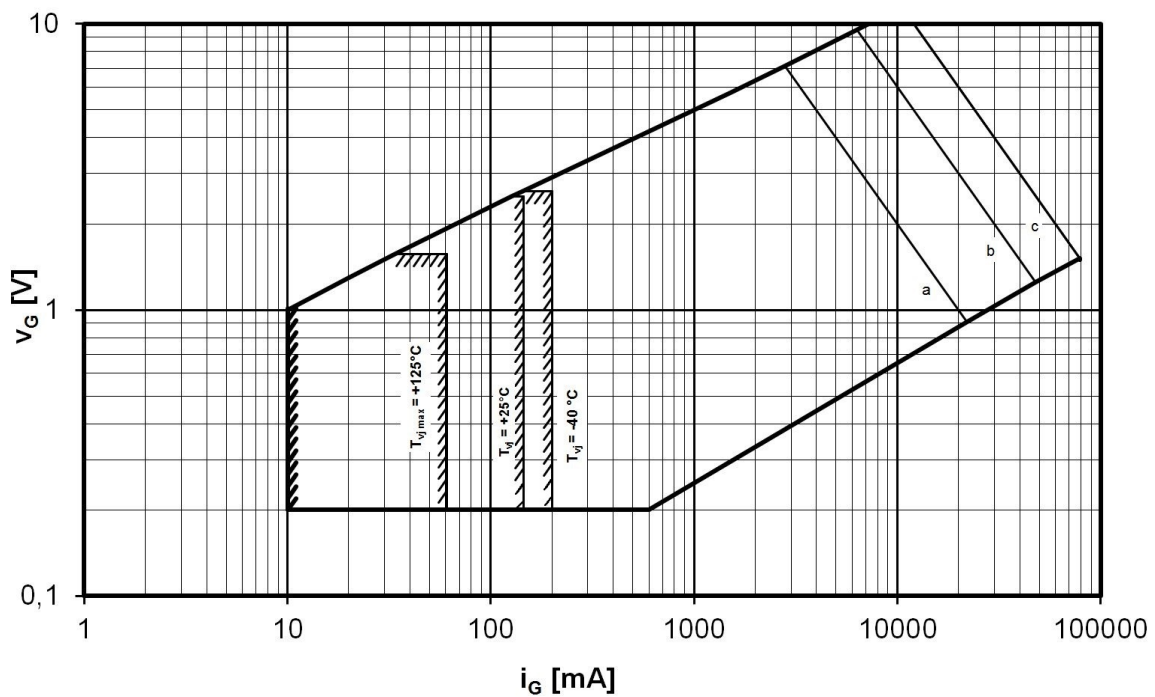
$$Z_{th \Theta rec} = Z_{thDC} + \Delta Z_{th \Theta rec}$$

$$Z_{th \Theta sin} = Z_{thDC} + \Delta Z_{th \Theta sin}$$



Transienter innerer Wärmewiderstand je Zweig / Transient thermal impedance per arm $Z_{thJC} = f(t)$

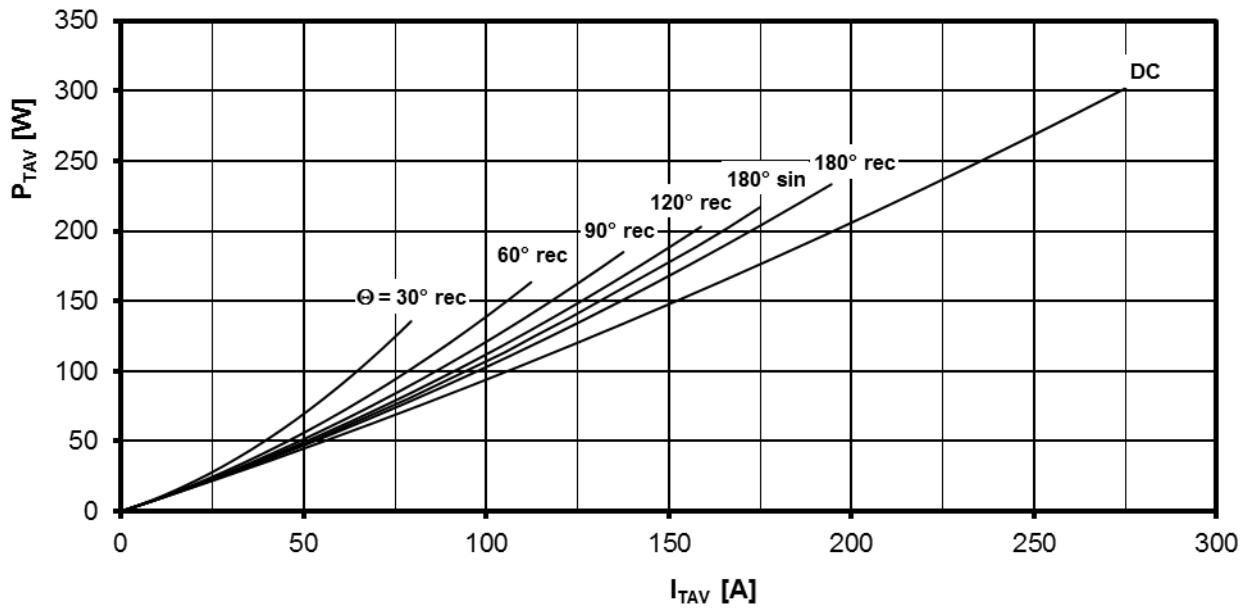
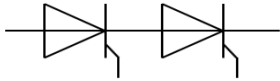
Parameter: Stromflußwinkel Θ / Current conduction angle Θ



Steuercharakteristik $v_G = f(i_G)$ mit Zündbereichen für $V_D = 12\text{ V}$
Gate characteristic $v_G = f(i_G)$ with triggering area for $V_D = 12\text{ V}$

Höchstzulässige Spitzensteuerverlustleistung / Maximum rated peak gate power dissipation $P_{GM} = f(t_g)$:

a – 20W/10ms b - 60W/500µs c - 120W/30µs

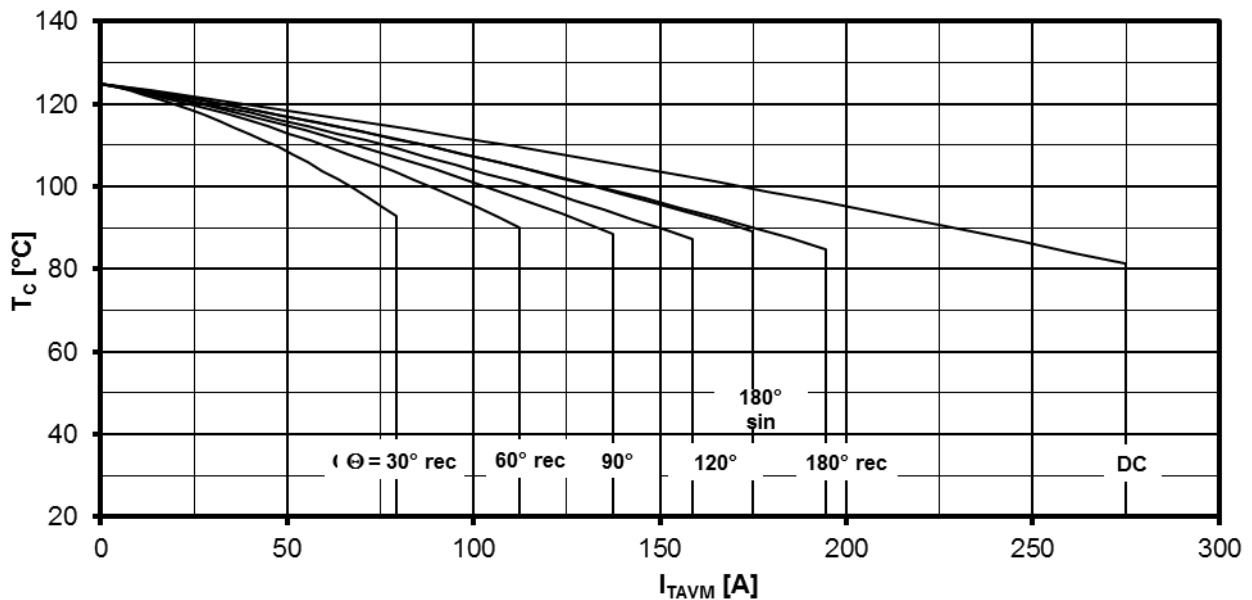


Durchlassverlustleistung je Zweig / On-state power loss per arm $P_{TAV} = f(I_{TAV})$

Strombelastung je Zweig / Current load per arm

Berechnungsgrundlage P_{TAV} (Schaltverluste gesondert berücksichtigen)
Calculation base P_{TAV} (switching losses should be considered separately)

Parameter: Stromflußwinkel / Current conduction angle Θ

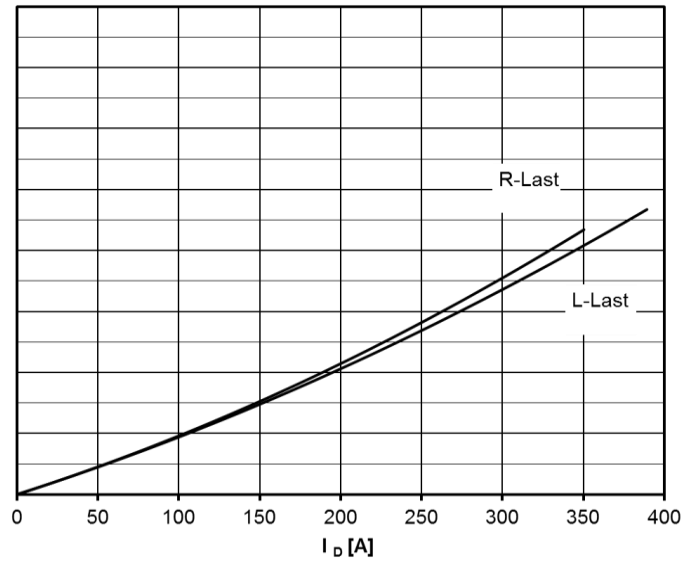
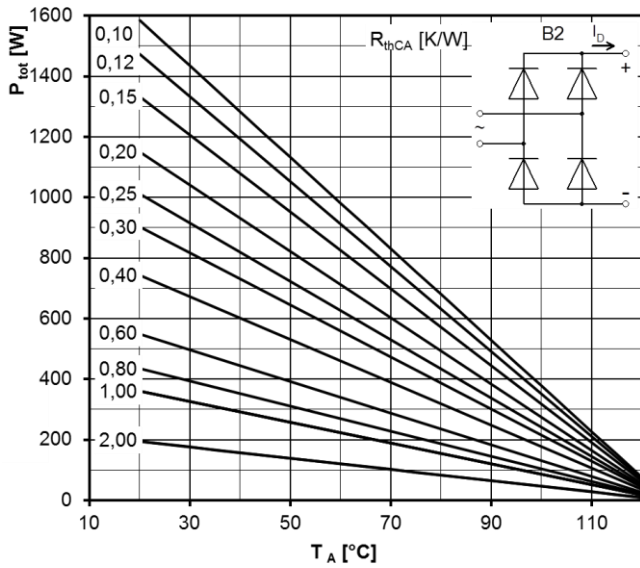
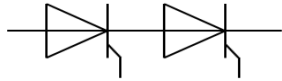


Höchstzulässige Gehäusetemperatur / Maximum allowable case temperature $T_C = f(I_{TAVM})$

Strombelastung je Zweig / Current load per arm

Berechnungsgrundlage P_{TAV} (Schaltverluste gesondert berücksichtigen)
Calculation base P_{TAV} (switching losses should be considered separately)

Parameter: Stromflußwinkel Θ / Current conduction angle Θ



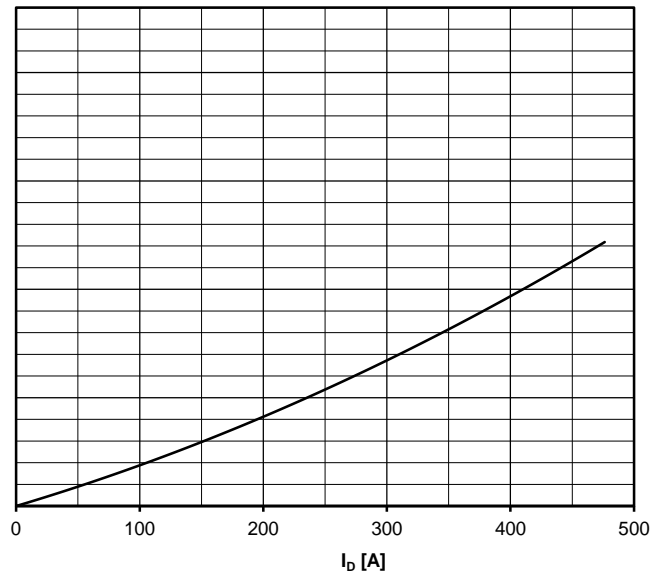
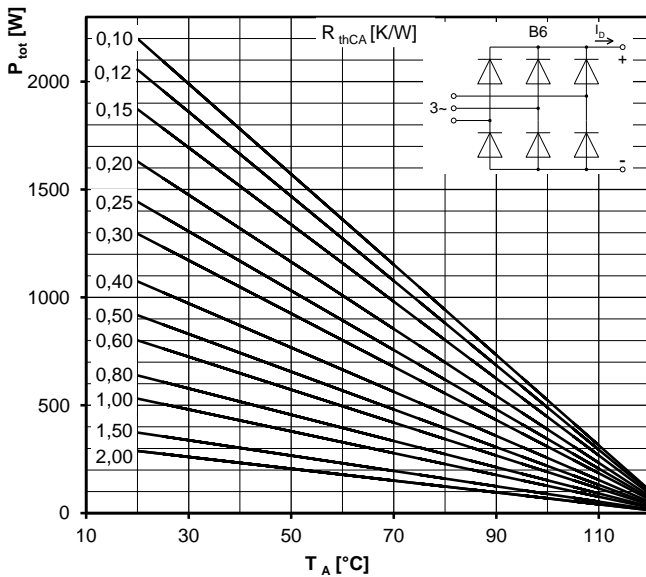
Höchstzulässiger Ausgangsstrom / Maximum rated output current I_D

B2- Zweipuls-Brückenschaltung / Two-pulse bridge circuit

Gesamtverlustleistung der Schaltung / Total power dissipation at circuit P_{tot}

Parameter:

Wärmewiderstand pro Element zwischen den Gehäusen und Umgebung /
Thermal resistance per chip cases to ambient R_{thCA}



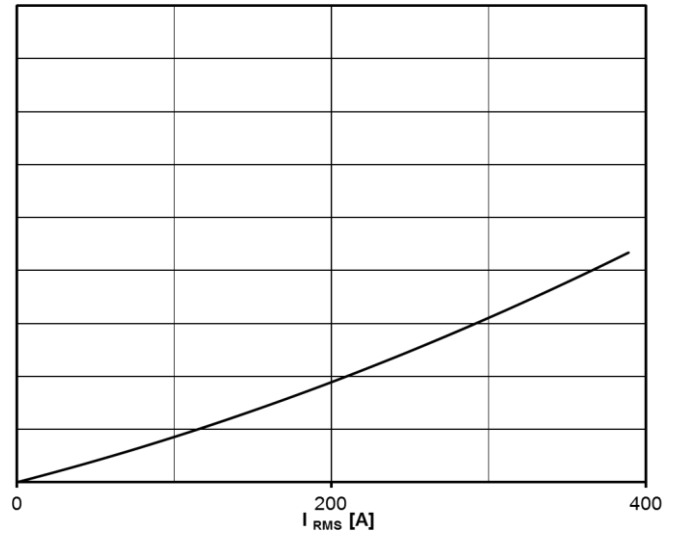
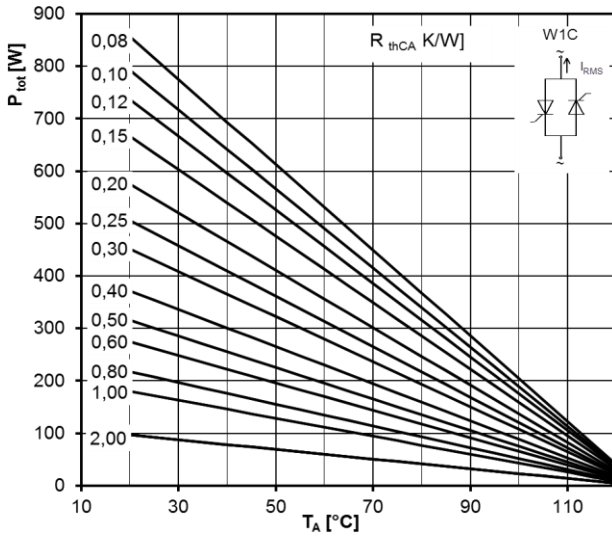
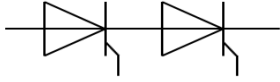
Höchstzulässiger Ausgangsstrom / Maximum rated output current I_D

B6- Sechspuls-Brückenschaltung / Six-pulse bridge circuit

Gesamtverlustleistung der Schaltung / Total power dissipation at circuit P_{tot}

Parameter:

Wärmewiderstand pro Element zwischen den Gehäusen und Umgebung /
Thermal resistance per chip cases to ambient R_{thCA}



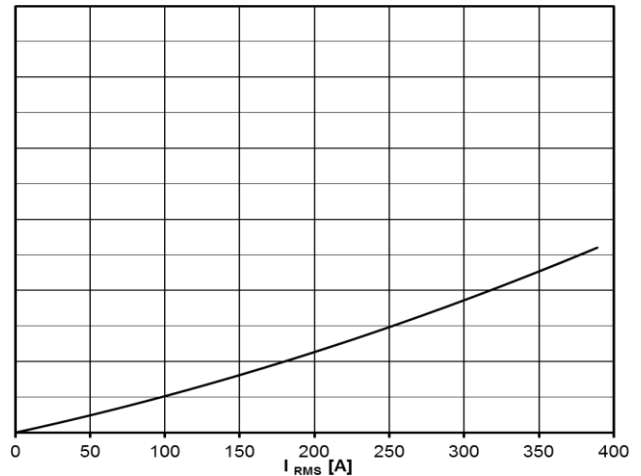
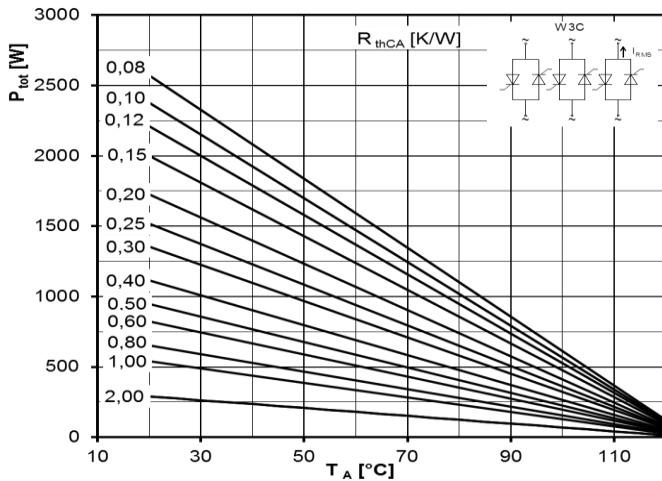
Höchstzulässiger Effektivstrom / Maximum rated RMS current I_{RMS}

W1C - Einphasen-Wechselwegschaltung / Single-phase inverse parallel circuit

Gesamtverlustleistung der Schaltung / Total power dissipation at circuit P_{tot}

Parameter:

Wärmewiderstand pro Element zwischen den Gehäusen und Umgebung /
Thermal resistance per chip cases to ambient R_{thCA}



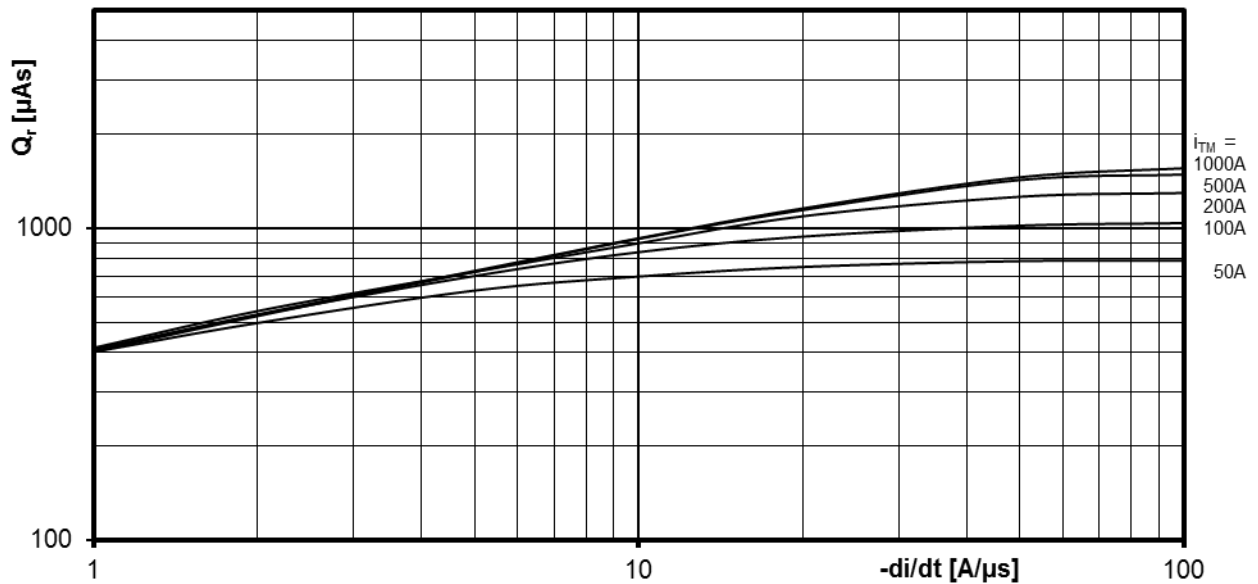
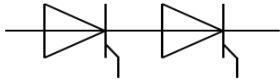
Höchstzulässiger Effektivstrom / Maximum rated RMS current I_{RMS}

W3C - Dreiphasen-Wechselwegschaltung / Three-phase inverse parallel circuit

Gesamtverlustleistung der Schaltung / Total power dissipation at circuit P_{tot}

Parameter:

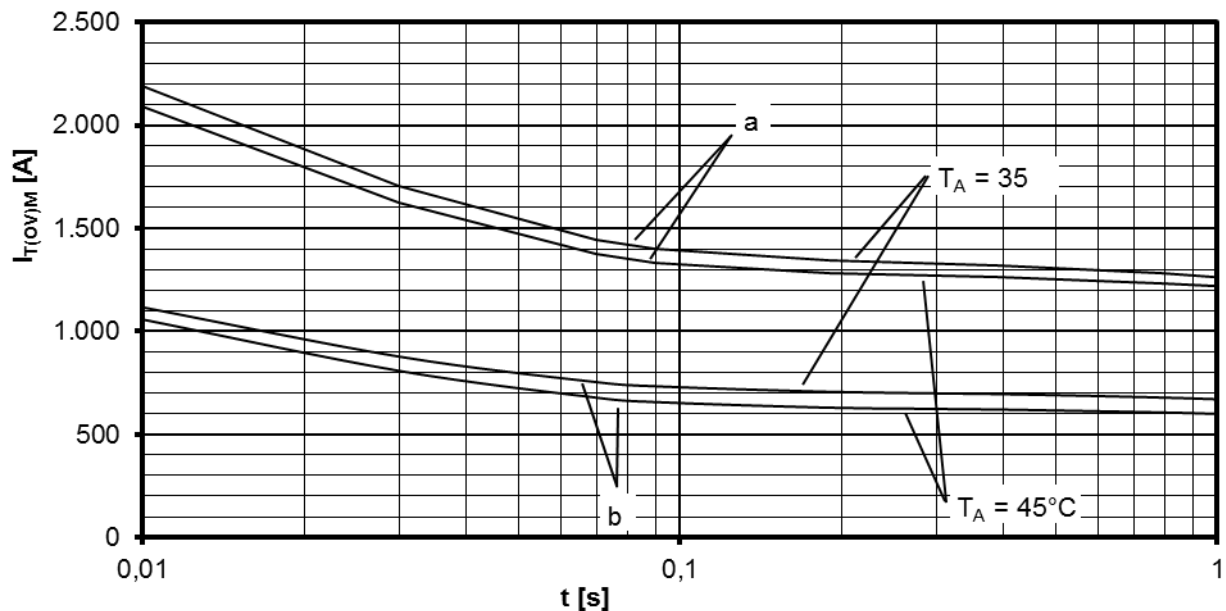
Wärmewiderstand pro Element zwischen den Gehäusen und Umgebung /
Thermal resistance per chip cases to ambient R_{thCA}



Sperrverzögerungsladung / Recovered charge $Q_r = f(-di/dt)$

$$T_{vj} = T_{vjmax}, v_R \leq 0,5 V_{RRM}, v_{RM} = 0,8 V_{RRM}$$

Parameter: Durchlaßstrom / On-state current i_{TM}



Grenzstrom / Maximum overload on-state current $I_{T(OV)M} = f(t), v_{RM} = 0,8 V_{RRM}$

a: Leerlauf / No-load conditions

b: nach Belastung mit I_{TAVM} / after load with I_{TAVM}

$T_A = 35^\circ\text{C}$, verstärkte Luftkühlung / Forced air cooling

$T_A = 45^\circ\text{C}$, Luftselbstkühlung / Natural air cooling